



November 2006

# FDB2614

## 200V N-Channel PowerTrench MOSFET

### General Description

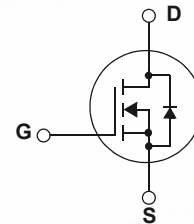
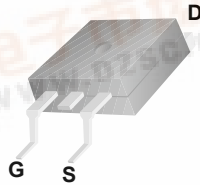
This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

### Description

- 62A, 200V,  $R_{DS(on)} = 22.9m\Omega @ V_{GS} = 10V$
- Fast switching speed
- Low gate charge
- High performance trench technology for extremely low  $R_{DS(on)}$
- High power and current handling capability

### Application

- PDP application



### Absolute Maximum Ratings

Symbol	Parameter	Ratings	Unit
$V_{DS}$	Drain-Source Voltage	200	V
$V_{GS}$	Gate-Source Voltage	$\pm 30$	V
$I_D$	Drain Current - Continuous ( $T_C = 25^\circ C$ ) - Continuous ( $T_C = 100^\circ C$ )	62 39.3	A A
$I_{DM}$	Drain Current - Pulsed (Note 1)	see Figure 9	A
$E_{AS}$	Single Pulsed Avalanche Energy (Note 2)	145	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5	V/ns
$P_D$	Power Dissipation ( $T_C = 25^\circ C$ ) - Derate above $25^\circ C$	260 2.1	W W/ $^\circ C$
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300	$^\circ C$

\*Drain current limited by maximum junction temperature

### Thermal Characteristics

Symbol	Parameter	Min.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	0.48	$^\circ C/W$
$R_{\theta JA}^*$	Thermal Resistance, Junction-to-Ambient*	--	40	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	62.5	$^\circ C/W$

\*When mounted on the minimum pad size recommended (PCB Mount)

FDB2614 200V N-Channel PowerTrench MOSFET



### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDB2614	FDB2614	D <sup>2</sup> -PAK	330mm	24mm	800

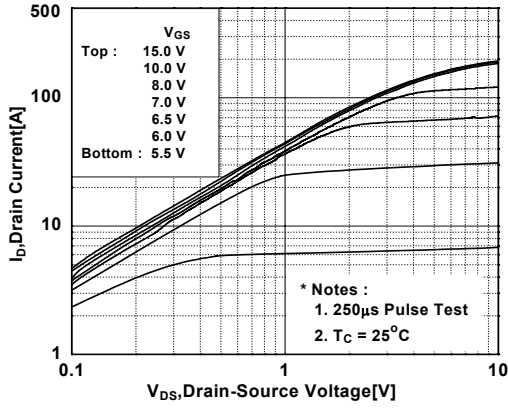
### Electrical Characteristics T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA, T <sub>J</sub> = 25°C	200	--	--	V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250μA, Referenced to 25°C	--	0.2	--	V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 200V, V <sub>GS</sub> = 0V V <sub>DS</sub> = 200V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C	--	--	1 500	μA μA
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30V, V <sub>DS</sub> = 0V	--	--	100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30V, V <sub>DS</sub> = 0V	--	--	-100	nA
<b>On Characteristics</b>						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	3.0	4.0	5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 31A	--	22.9	27	mΩ
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 10V, I <sub>D</sub> = 31A (Note 4)	--	72	--	S
<b>Dynamic Characteristics</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V f = 1.0MHz	--	5435	7230	pF
C <sub>oss</sub>	Output Capacitance		--	505	675	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		--	110	165	pF
<b>Switching Characteristics</b>						
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 100V, I <sub>D</sub> = 62A V <sub>GS</sub> = 10V, R <sub>GEN</sub> = 25Ω (Note 4, 5)	--	77	165	ns
t <sub>r</sub>	Turn-On Rise Time		--	284	560	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		--	103	220	ns
t <sub>f</sub>	Turn-Off Fall Time		--	162	335	ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> = 100V, I <sub>D</sub> = 62A V <sub>GS</sub> = 10V (Note 4, 5)	--	76	99	nC
Q <sub>gs</sub>	Gate-Source Charge		--	35	--	nC
Q <sub>gd</sub>	Gate-Drain Charge		--	18	--	nC
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current		--	--	62	A
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current		--	--	186	A
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0V, I <sub>S</sub> = 62A	--	--	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0V, I <sub>S</sub> = 62A	--	145	--	ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI <sub>F</sub> /dt = 100A/μs (Note 4)	--	0.81	--	μC

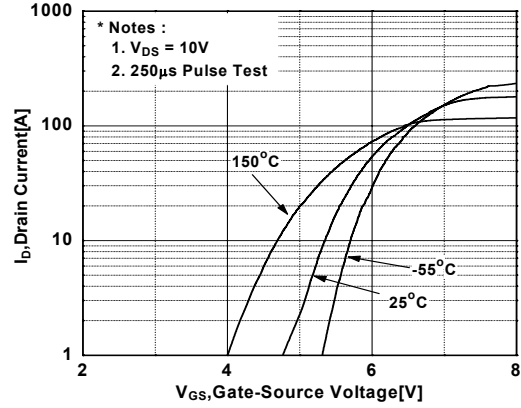
**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L = 1mH, I<sub>AS</sub> = 17A, V<sub>DD</sub> = 50V, R<sub>G</sub> = 25Ω, Starting T<sub>J</sub> = 25°C
3. I<sub>SD</sub> ≤ 62A, di/dt ≤ 100A/μs, V<sub>DD</sub> ≤ BV<sub>DSS</sub>, Starting T<sub>J</sub> = 25°C
4. Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%
5. Essentially Independent of Operating Temperature Typical Characteristics

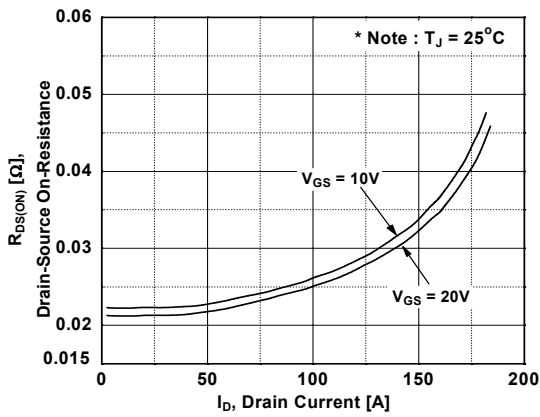
**Figure 1. On-Region Characteristics**



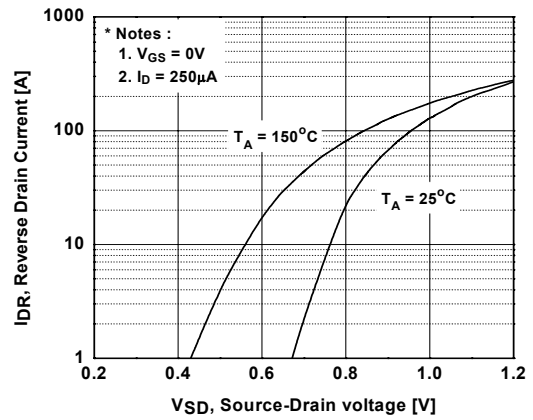
**Figure 2. Transfer Characteristics**



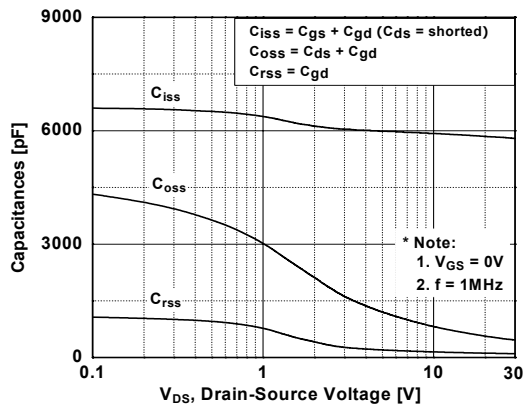
**Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage**



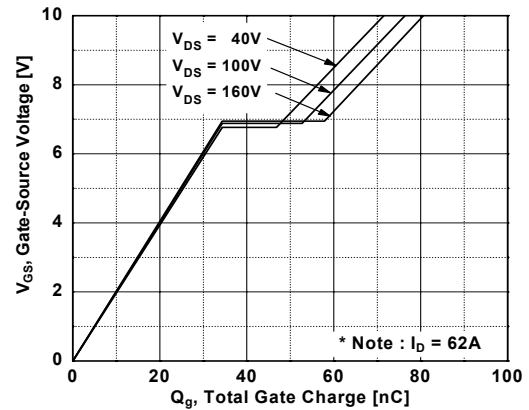
**Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature**



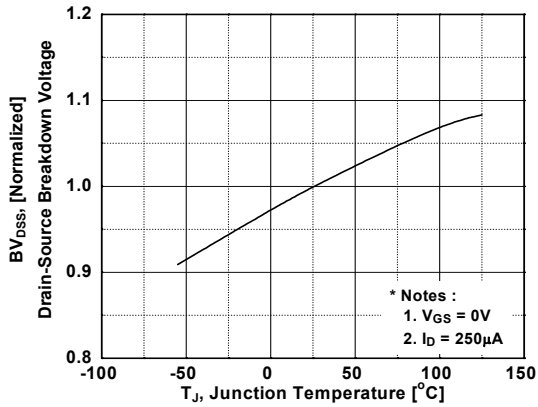
**Figure 5. Capacitance Characteristics**



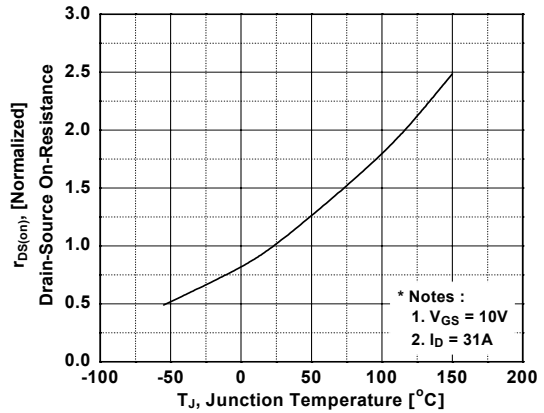
**Figure 6. Gate Charge Characteristics**



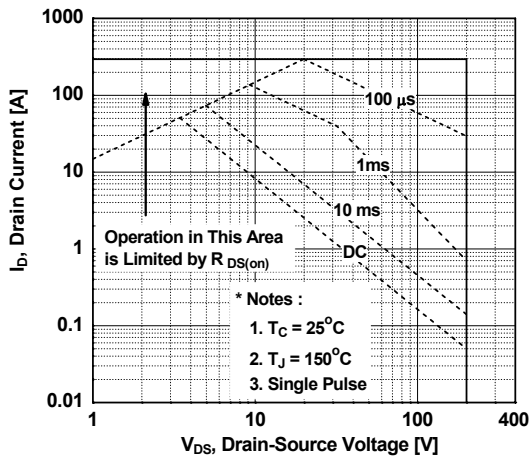
**Figure 7. Breakdown Voltage Variation vs. Temperature**



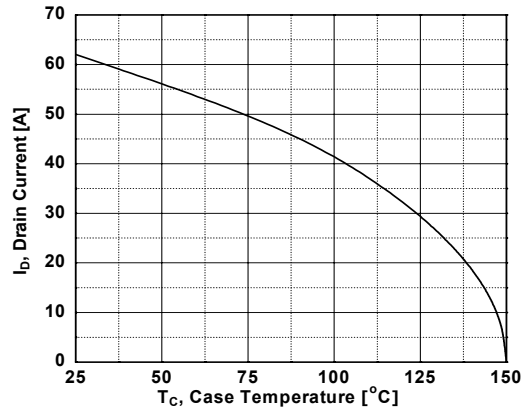
**Figure 8. On-Resistance Variation vs. Temperature**



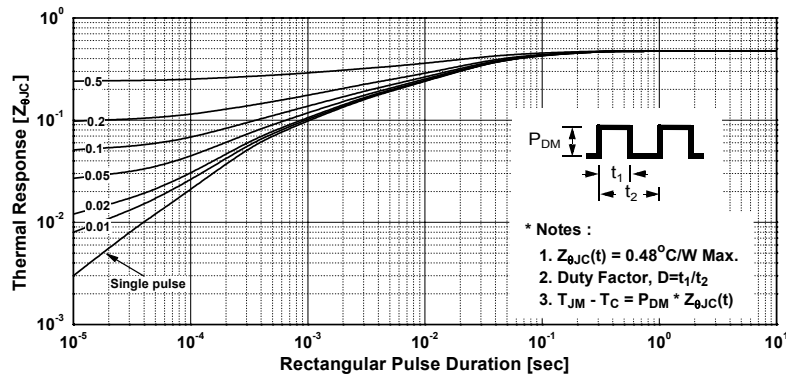
**Figure 9. Maximum Safe Operating Area**



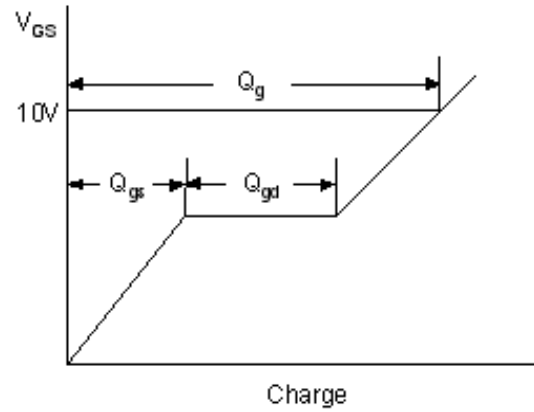
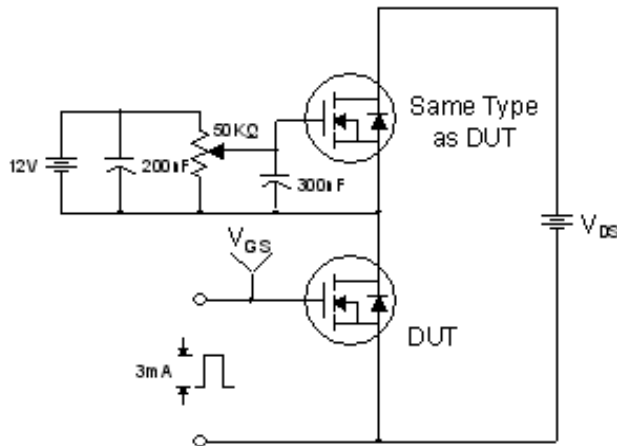
**Figure 10. Maximum Drain Current vs. Case-Temperature**



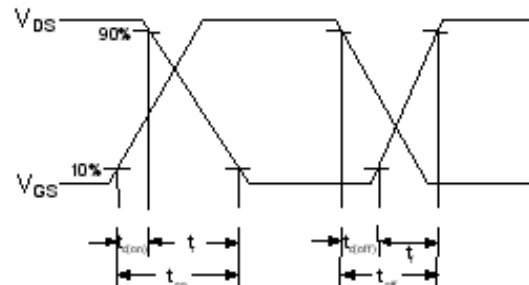
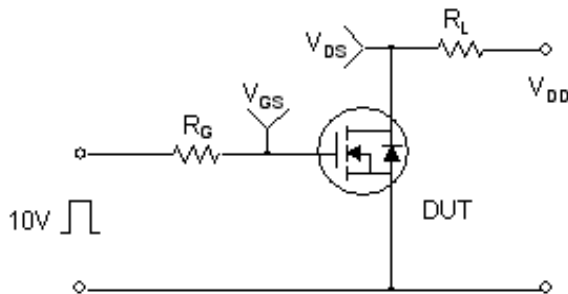
**Figure 11. Transient Thermal Response Curve**



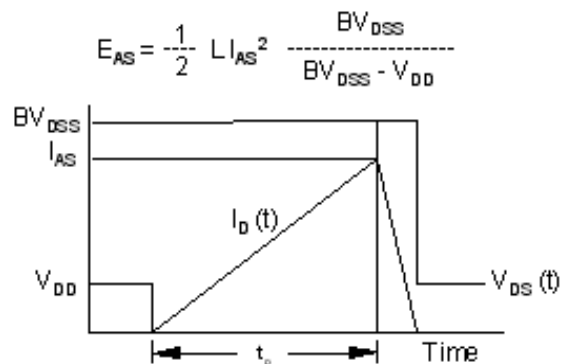
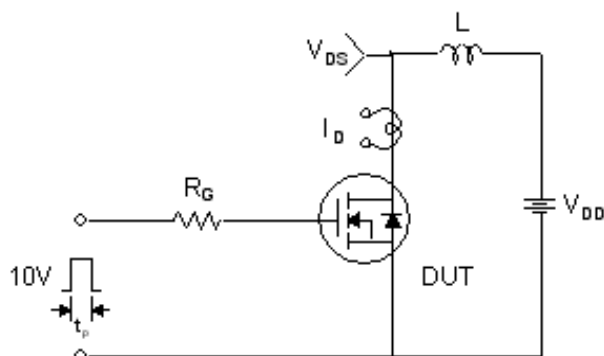
**Gate Charge Test Circuit & Waveform**



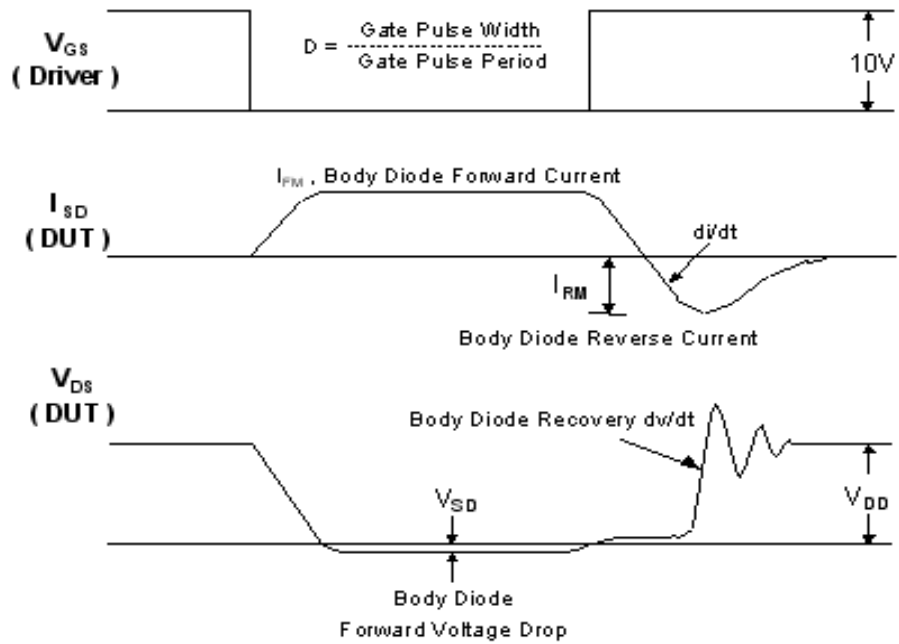
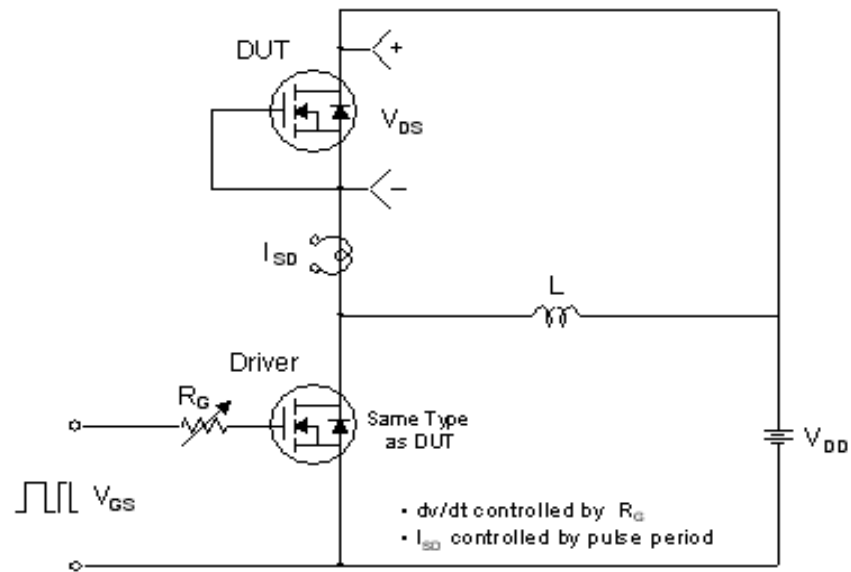
**Resistive Switching Test Circuit & Waveforms**



**Unclamped Inductive Switching Test Circuit & Waveforms**

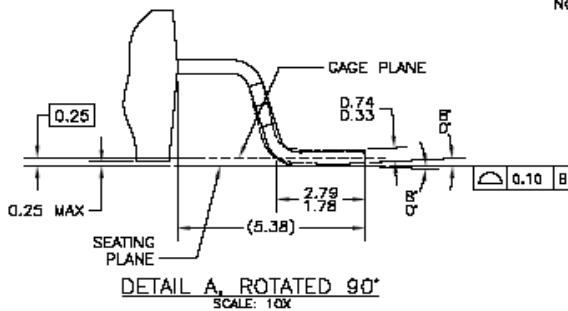
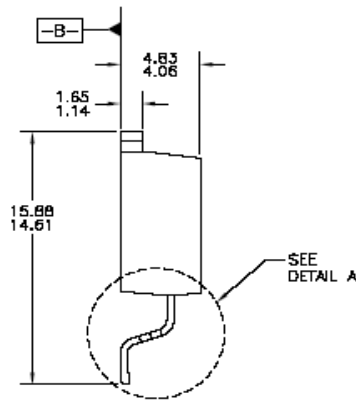
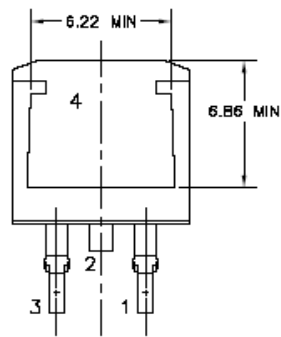
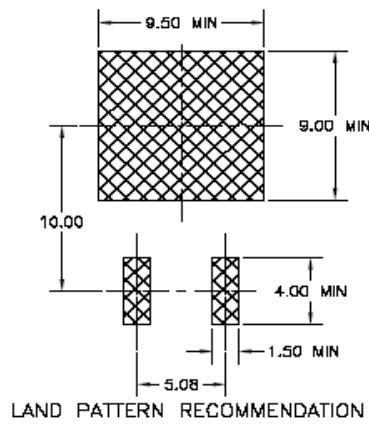
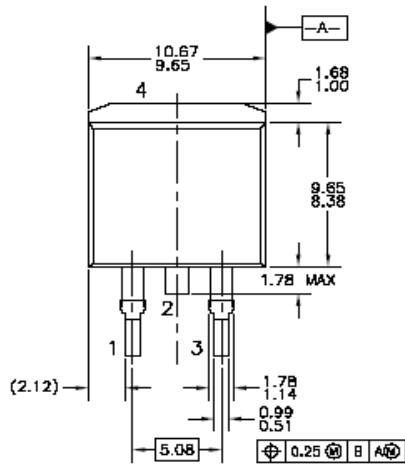


Peak Diode Recovery dv/dt Test Circuit & Waveforms



# Package Dimensions

## D2-PAK



- NOTES: UNLESS OTHERWISE SPECIFIED
- A) ALL DIMENSIONS ARE IN MILLIMETERS.
  - B) REFERENCE JEDEC, TO-263, ISSUE D, VARIATION AB, DATED JULY 2003.
  - C) DIMENSIONING AND TOLERANCING PER ANSI Y14.5M - 1982.
  - D) LOCATION OF THE PIN HOLE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE).
  - E) PRESENCE OF TRIMMED CENTER LEAD IS OPTIONAL.

T02B3AD2REVD

Dimensions in Millimeters

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Bottomless™	GTO™	OPTOLOGIC®	SPM™	VCX™
Build it Now™	HiSeC™	OPTOPLANAR™	Stealth™	Wire™
CoolFET™	I <sup>2</sup> C™	PACMAN™	SuperFET™	
CROSSVOLT™	i-Lo™	POP™	SuperSOT™-3	
DOME™	ImpliedDisconnect™	Power820417™	SuperSOT™-6	
EcoSPARK™	IntelliMAX™	PowerEdge™	SuperSOT™-8	
E <sup>2</sup> CMOS™	ISOPLANAR™	PowerSaver™	SyncFET™	
EnSigna™	LittleFET™	PowerTrench®	TCM™	
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FAST®	MicroFET™	QS™	TinyBuck™	
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FRFET™	MSX™	RapidConfigure™	TinyLogic®	
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